

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	17	epitaxial adj dielectric adj film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 12:25
S2	118	epitaxial adj dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 10:35
S3	158404	sic or silicon adj carbide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 16:36
S4	43	S2 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 12:17
S5	2	S1 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 12:25
S6	2630	high adj k adj dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 13:11
S7	126269	cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 13:11
S8	4296	sic adj substrate or silicon adj carbide adj substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 13:00

S9	334	S7 and S8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 13:12
S10	182	S6 and S9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 13:13
S11	3224	(sic or silicon adj carbide) and S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 13:23
S12	296	S6 and S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 13:43
S13	532	cree.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 13:43
S14	10	S7 and S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 13:43
S15	7	(epitaxial adj grown) near4 dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 13:56
S16	46534	ferroelectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 13:56

S17	35	(sic adj substrate or silicon adj carbide adj substrate) and cmos and S16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 14:00
S18	2	("6660598").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/28 14:00
S19	2	("6552403").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/28 16:32
S20	1762	crystalline adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 16:35
S21	91699	sic or silicon adj carbide and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 16:36
S22	481	(sic or silicon adj carbide) and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 16:36
S23	193	(sic adj substrate or silicon adj carbide adj substrate) and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 16:36
S24	3	silicon adj carbide adj gate adj dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 08:49

S25	0	silicon adj carbide adj gate adj insula????	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 08:49
S26	10	silicon adj carbide adj gate adj insulator	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 08:49
S27	5	("6281521").URPN.	USPAT	OR	ON	2005/07/29 08:55
S28	121	barium adj strontium adj titanate near4 (epitaxial or crystalline or structure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 09:04
S29	295	perovskite near4 (bst or barium adj strontium adj titanate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 09:05
S30	4	silicon adj carbide adj gate adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 12:06
S31	1573	sioc	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 12:38
S32	1805	sioc or silicon adj carbon adj oxide or silicon adj carbide adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 12:39
S33	113	crystalline and dielectric and S32	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 12:43

S34	848	silicon adj oxycarbide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 12:44
S35	99	cmos and S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 12:44
S36	1	(sic adj substrate or silicon adj carbide adj substrate) and S35	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 12:44
S37	0	"mirabedini.in"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 12:59
S38	24	mirabedini.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 12:59
S39	2	carbide and S38	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 13:00
S40	10885	lsi.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 13:00
S41	1	(sic adj substrate or silicon adj carbide adj substrate) and S40	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 13:01

S42	184	(438/105).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/13 10:26
S43	4679	sic adj substrate or silicon adj carbide adj substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 08:13
S44	413	epitaxial adj dielectric or epitaxial adj gate adj oxide or epitaxial adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 08:14
S45	19	S43 and S44	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 08:15
S46	0	silicon adj carbide adj substrate near6 cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 08:16
S47	200	(438/105).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/13 10:36
S48	0	epitaxial adj dielectric and S47	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 10:35
S49	234	pervoskite	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 10:36

S50	0	S47 and S49	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 10:36
S51	18309	perovskite	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 10:42
S52	1	S47 and S51	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 10:37
S53	696815	cms	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 10:37
S54	134694	cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 10:37
S55	1401	S51 and S54	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 10:37
S56	266011	carbide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 10:38
S57	338	S55 and S56	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 10:38

S58	22	perovskite near6 gate adj dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 10:43
S59	1	S56 and S58	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 10:45
S60	4679	silicon adj carbide adj substrate or sic adj substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 10:45
S61	221	S51 and S60	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 10:45
S62	194	S54 and S61	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 10:46
S63	12	("20020022344"   "20020053318"   "20020056519"   "6326285"   "6328796"   "6344404"   "6352909"   "6355541"   "6387829"   "6426248"   "6489241"   "6562720").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/01/13 10:55
S64	1	("6638872").URPN.	USPAT	OR	ON	2006/01/13 10:57